CLAIMS

What is claimed is:

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7. A system comprising:

a wafer comprising at least one layer;

a depth measurer to measure a thickness of a selected region of an exposed layer of the wafer; and

an etch tool to selectively remove a thickness of the exposed layer in response to the measured thickness being greater than a specified thickness of the exposed layer of the selected region.

8. The system of Claim 7, further comprising a control system to store a map associating thicknesses of the exposed layer for at least two regions of the exposed layer.

9. The system of Claim 7, wherein the exposed layer comprises a silicon layer.

10. The system of Claim 7, wherein the depth measurer comprises a spectroscopic elipsometry device.

11. The system of Claim 7, wherein the etch tool comprises a plasma generator.

12. The system of Claim 7, wherein the wafer comprises a silicon-on-insulator device further comprising a silicon layer separated from a substrate by an oxide layer.

13. An apparatus comprising:

a substrate;

a silicon layer; and

an oxide layer electrically insulating the silicon layer from the substrate, wherein a thickness of the silicon layer is formed by removing at least a portion of the silicon layer using a plasma generator.

14. The apparatus of Claim 13, wherein an amount to remove from a surface of the silicon layer is determined using a spectroscopic elipsometry device.

15. The apparatus of Claim 14, wherein the plasma generator removes at least a portion of the silicon layer based upon a map specifying thicknesses of at least two regions of the silicon layer.